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<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		Applicati n Number	10/693,847
		Filing Date	10/20/03
		First Named Inventor	August et al.
		Group Art Unit	Not Yet Assigned
		Examiner Name	Not Yet Assigned
		Attorney Docket Number	84,355
Sheet 2	of 2		

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No.¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	²
		MCGREGOR et al, "Self-Biased Boron-10-Coated High-Purity Epitaxial GaAs Thermal Neutron Detector" IEEE transactions on nuclear science, vol. 47, no., August 2000	
		MCGREGOR et al, "Recent Results From Thin-Film-Coated Semiconductor Neutron Detectors" X-Ray and Gamma-Ray Detector and Application.IV., vol. 4784 (2002).	
		HAQUE et al, "Neutron dosimetry employing soft errors in dynamic random access memories" Phys. Med. Biol., 1989 vol. 34, no 9, 1195-1202 Printed in the UK	
		PHILLIPS et al, "Feasibility of a Neutron Detector-Dosimeter Based on Single-Event Upsets in Dynamic Random-Access Memories" Radiation Protection Dosimetry vol. 101, nos. 1-4, pp. 129-132 (2002) Nuclear Technology Publishing	
		ROBERTSON et al, "A class of boron-rich solid-state neutron detectors" Applied Physics Letters volume 80, number 19, 13 May 2002	
		GUARINI et at, "Electrical Integrity of State-of-the-Art 0.13 um SOI CMOS Devices and Circuits Transferred for Three-Dimensional (3D) Integrated Circuit (IC) Fabrication" 0-7803-7462-2/02 2002 IEEE	
		ARITA el al, "Experimental Investigation of Thermal Neutron-Induced Single Event Upset in Static Random Access Memories" Jpn. J. Appl. Phys Vol. 40 (2001) pp. L151-L153 Part 2, No. 2B, 15 February 2001	
		HUGHES et al, "Radiation Effects and Hardening of Mos Technology: Devices and Circuits" Preprint IEEE Trans. Nucl. Sci. June 2003	
		LUND et al. "Neutron Dosimeter Using a Dynamic Random Access Memory as a Sensor" IEEE Transactions on Nuclear Science, Vol. 33. No. 1, February 1996	
		PETERSEN et al. "Calculation of Cosmic-Ray Induced Soft Upsets and Scaling in VLSI Devices*" IEEE Transaction on Nuclear Science, Vol. NS-29, No. 6, December 1982.	
		DAVIS "Use of Computer Memory Chips as The Basis For a Digital Albedo Neutron Dosimeter*" Health Physics Vol. 49, No. 2 (August), pp. 259-265, 1985 Printed in the U.S.A.	

Examiner Signature		Date Considered	
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¹ Unique citation designation number. ² Applicant is to place a check mark here if English language Translation is attached.

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